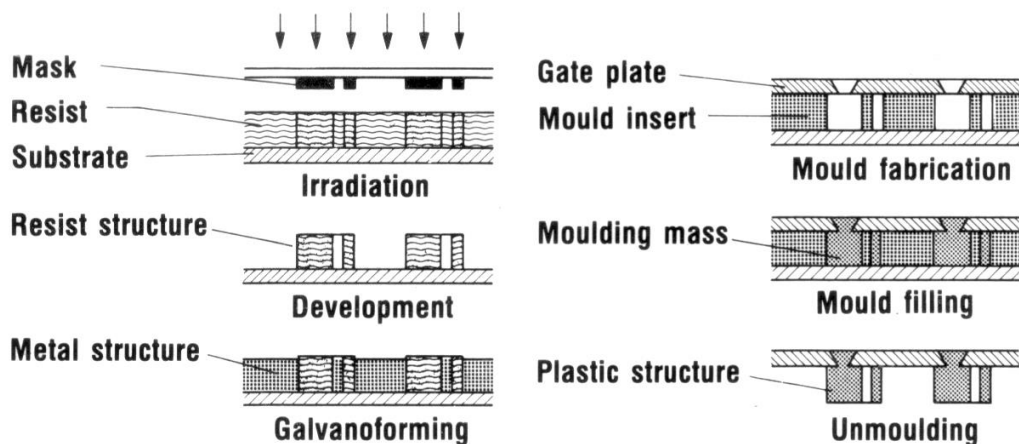


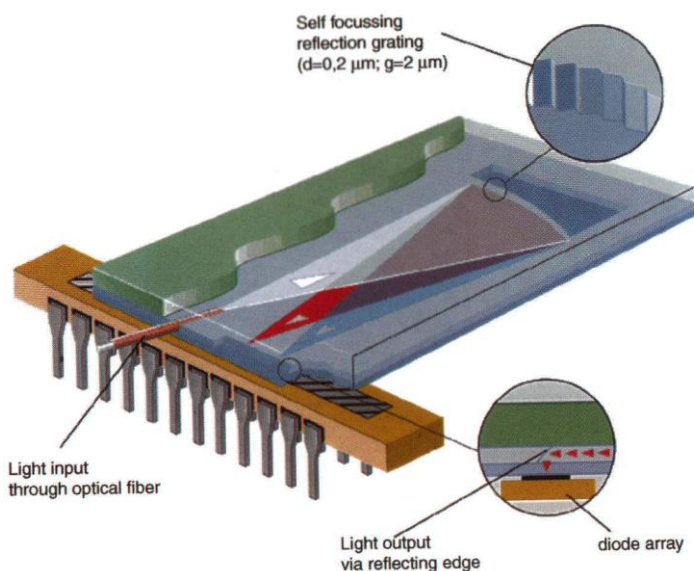
E1 LIGA process



LIGA process by X ray exposure, electroplating and plastic molding (Germany)



Reference : E.W.Becker, W.Ehrfeld, P.Hagmann, A.Maner and D.Munchmeyer, Fabrication of Microstructures with High Aspect Ratios and Great Structural Heights by Synchrotron Radiation Lithography, Galvanoforming, and Plastic Moulding (LIGA Process), Microelectronic Engineering, 4 (1986) pp.35–56



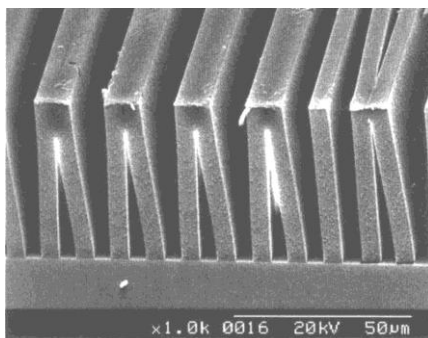
Micro spectrometer fabricated with LIGAprocess (Micro Parts, Germany)



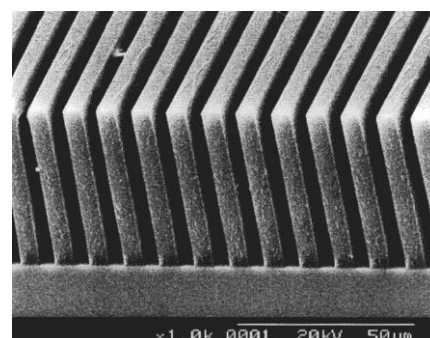
Reference : Microspectrometer Fabricated by the LIGA Process, Interdisciplinary Science Review, 18 (1993) pp.273–279



SORリング(電子蓄積リング)



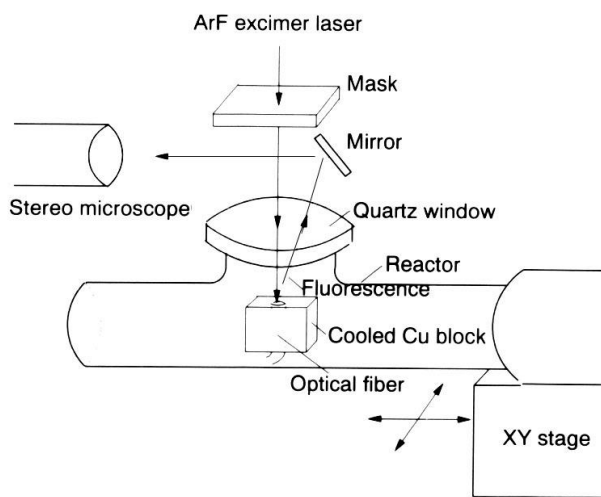
Adhesion during drying



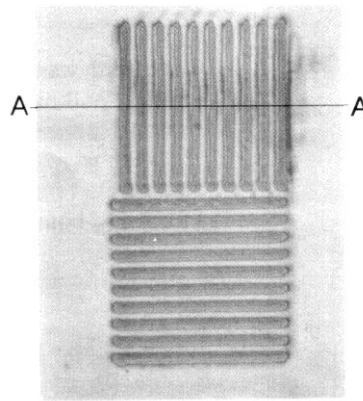
Drying using low surface tension liquid
SORTEC)

Reference : S.Watanabe, M.Esashi and Y.Yamashita, Fabrication Methods for High Aspect Ratio Microstructures, J.of Intelligent Material Systems and Structures, 8 (1997) pp.173–176

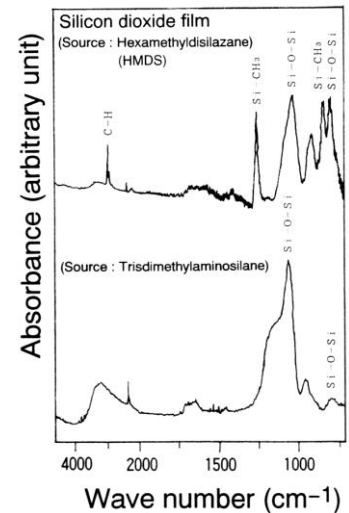
E2 Laser processes and stealth dicing



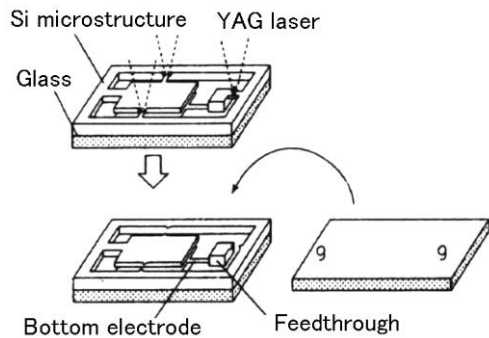
Laser projection CVD



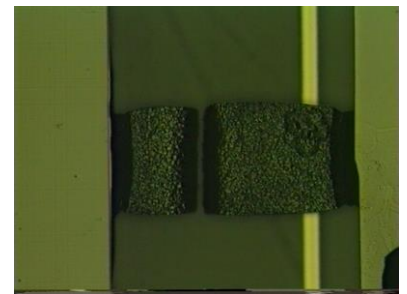
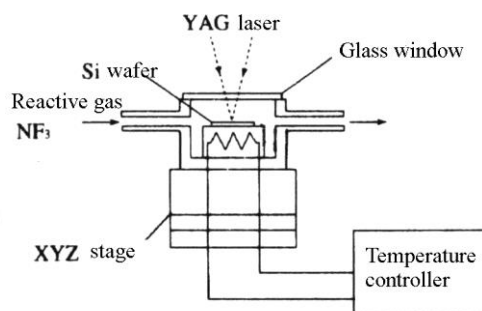
Pressure of HMDS : 470Pa
Pressure of O₂ : 67Pa
Substrate temp. : 2°C
Laser irradiation time : 2min



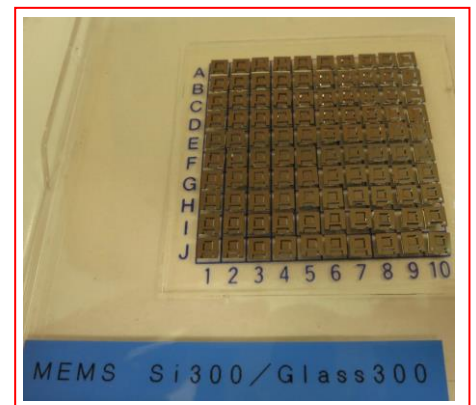
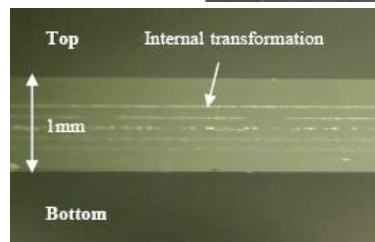
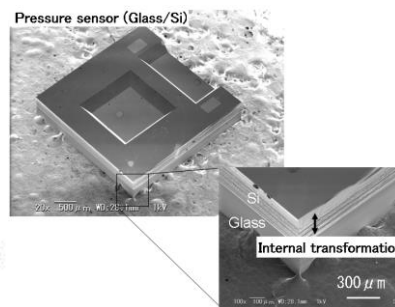
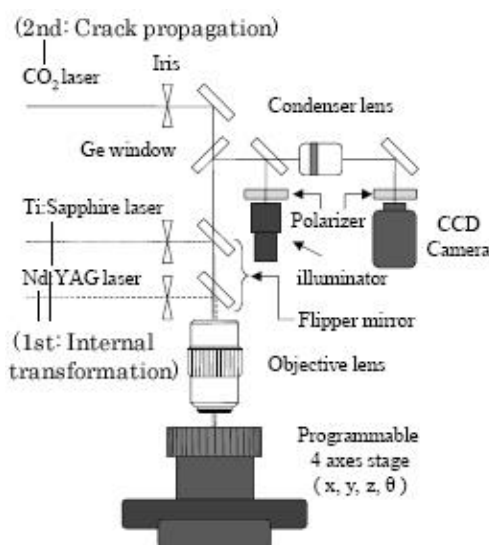
Reference : K.Takashima, K.Minami, M.Esashi and J.Nishizawa, Laser Projection CVD Using the Low Temperature Condensation Method, Applied Surface Science, 79/80 (1994) pp.366-374



Laser assisted Si etching



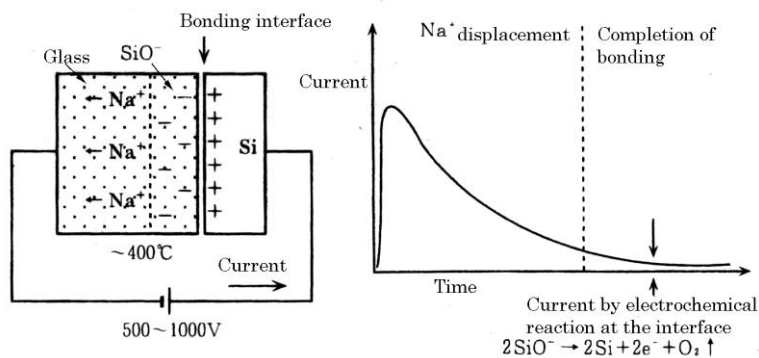
Reference : K.Minami, Y.Wakabayashi, M.Yoshida, K.Watanabe and M.Esashi, YAG Laser-Assisted Etching of Silicon for Fabricating Sensors and Actuators, J. of Micromechanics and Microengineering, 3 (1993) pp.81-86



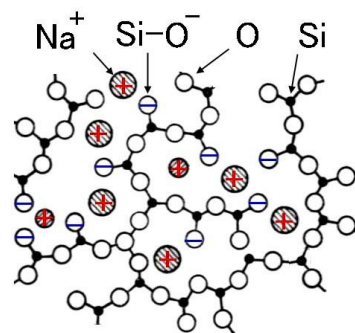
Laser (stealth) dicing of Si-glass structure (Tohoku Univ. – Inst. For Laser Tech.)

Reference : M.Fujita, Y.Izawa, Y.Tsurumi, S.Tanaka, H.Fukushi, K.Sueda, Y.Nakata, M.Esashi and N.Miyanaga, Debris-free Low-stress High-speed Laser Assisted Dicing for Multi-layered MEMS, Trans. IEE of Japan, 130-E (2010) pp.118-123

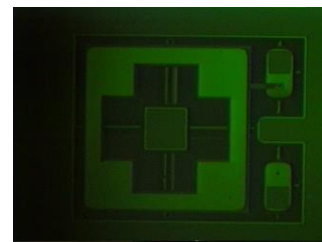
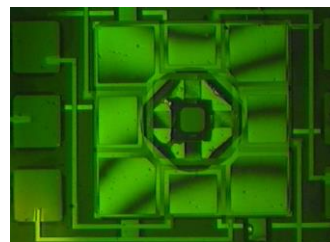
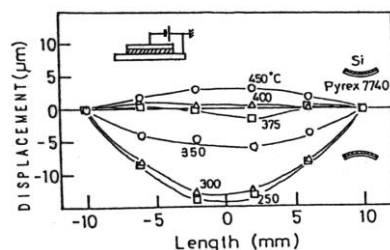
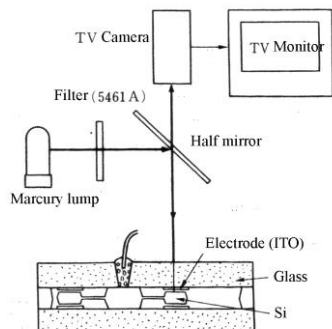
E3 Anodic bonding



Principle of anodic bonding

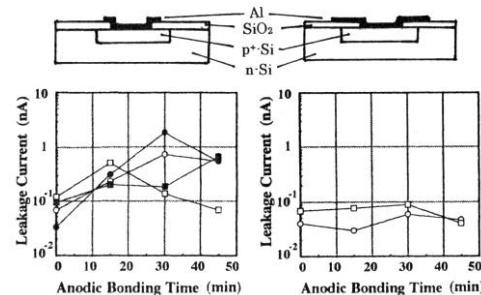
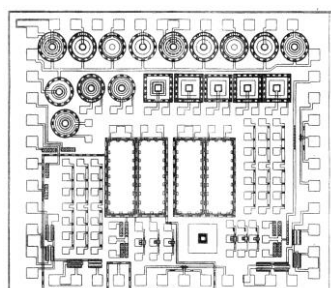
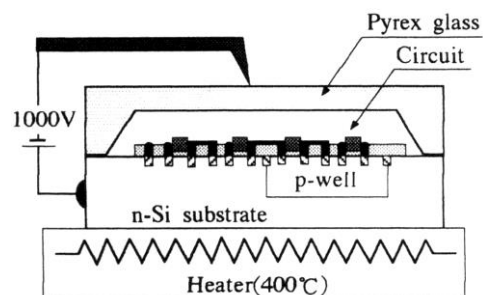


Molecular structure of glass



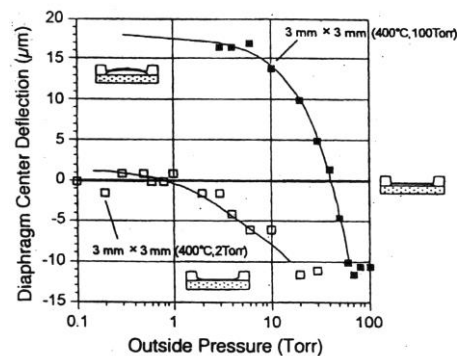
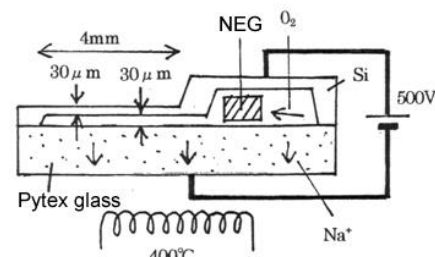
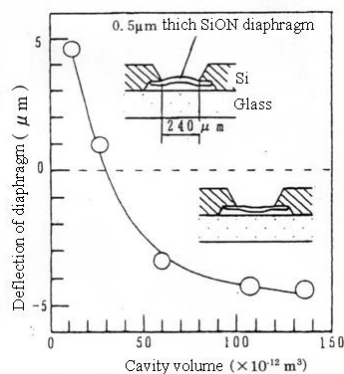
Distortion after anodic bonding

Reference : Y.Shoji, K.Minami, M.Esashi, Glass-silicon Anodic Bonding for the Reduction of Structural Distortion, Trans. IEE of Japan, 115-A (1995) pp.1208-1213



Influences of anodic bonding to CMOS circuit

Reference : M.Shirai, M.Esashi, Circuit Damage by Anodic Bonding, Technical Report IEE of Japan, ST-92-7 (1992) pp.9-17



Vacuum packaging and pressure controlled packaging (right) by anodic bonding

Reference : N.Ura, K.Nakaichi, K.Minami, M.Esashi, Vacuum Packaging by Anodic Bonding, The 11th Sensor Symposium (1992) p.63

M.Esashi, Vacuum Packaging Technology for Microsensors, Trans. IEE of Japan, 120-E (2000) pp.310-314

E4 Anodically bondable LTCC with electrical feedthrough (Nikko)

1. Green sheet



2. Punching



3. Plugging holes with Au paste



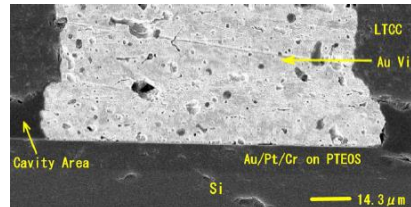
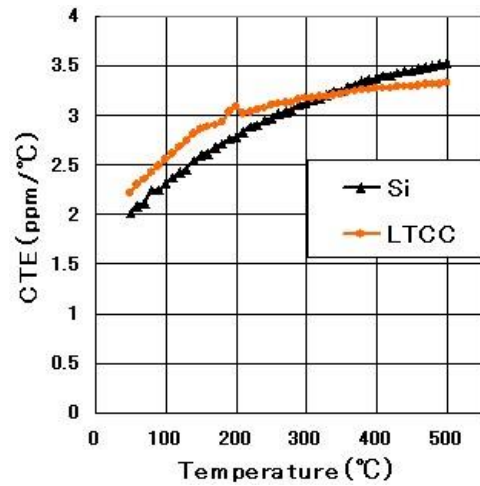
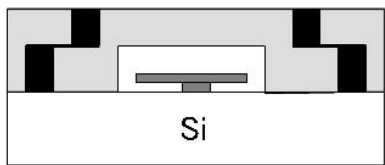
4. Laminating



5. Sintering



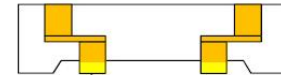
6. Anodic bonding



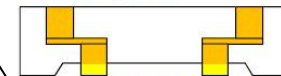
1. Production of LTCC wafer



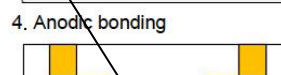
2. Wet etching of LTCC wafer



3. Wafer alignment

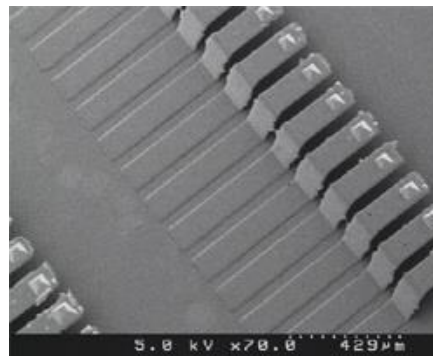
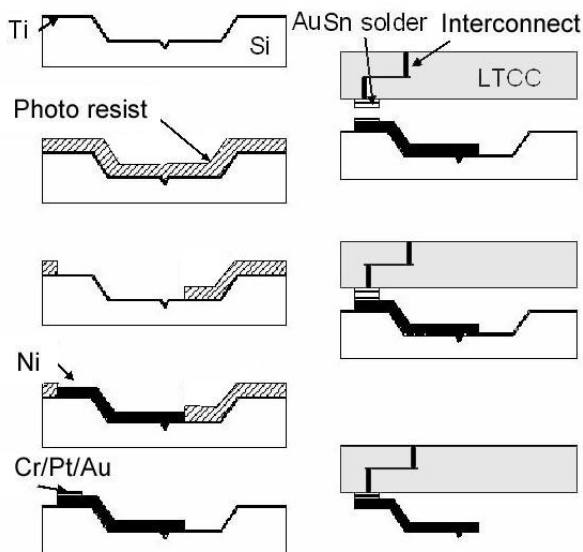


4. Anodic bonding

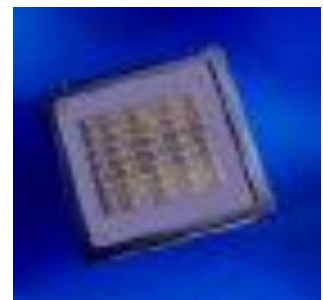


Anodically bondable LTCC (Low Temperature Co-fired Ceramics) with electrical feedthrough and electrical interconnection using porous gold (Nikko – Tohoku Univ.)

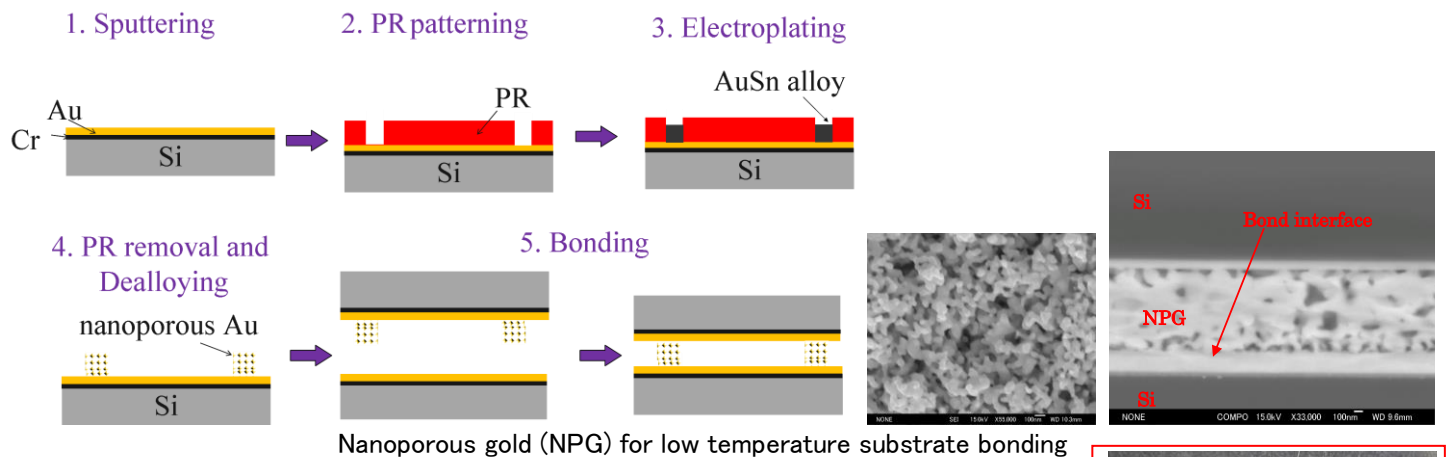
Reference : M.Mohri, A.Okada, H.Fukushi, M.Esashi and S.Tanaka, Packaging Technology for Hermetic Sealing with Electrical Connection Using Anodically-Bondable LTCC Substrate with Etched Cavities, The 28th Sensor Symposium on Sensors, Micromachines and Applied Systems (2011) p.62



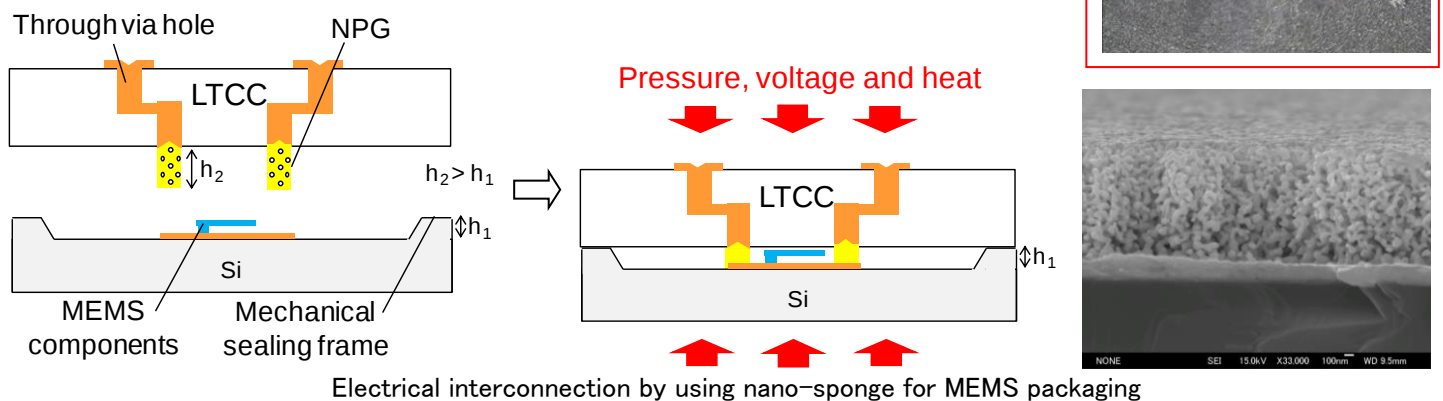
Probe card using LTCC for wafer-level burn-in test



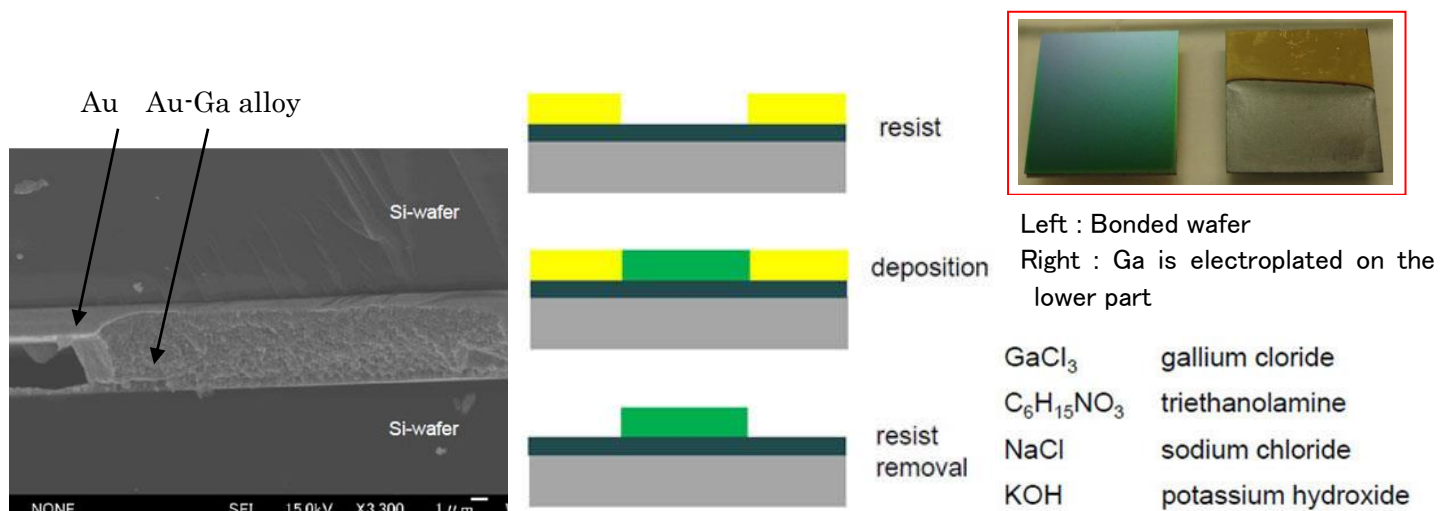
Reference : S.-H.Choe, S.Tanaka and M.Esashi, A Matched Expansion MEMS Probe Card with Low CTE LTCC Substrate, IEEE International Test Conference 2007 (2007) Paper 20.2



Reference : W. -S. Wang, Y. -C. Lin, L. Y. Chen, M. W. Chen, T. Gessner and M. Esashi, Demonstration of Substrate Bonding utilizing Au Film and Nanoporous Gold Structures, Proceedings of the International Conference on Wafer Bond ' 11, Dec. 7-8 (2011)



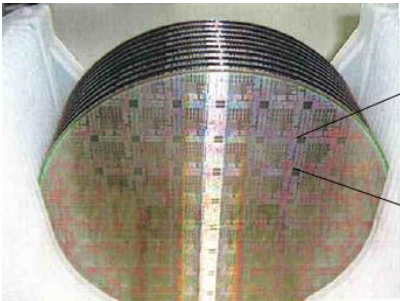
Reference : Y. -C. Lin, W. -S. Wang, L. Y. Chen, M. W. Chen, T. Gessner and M. Esashi, Anodically-bondable LTCC substrates with Novel nano-structured electrical Interconnection for mems packaging, Proceedings of the international conference on solid-state sensors and actuators (Transducers ' 11), June 5-9 (2011) pp. 2351-2354



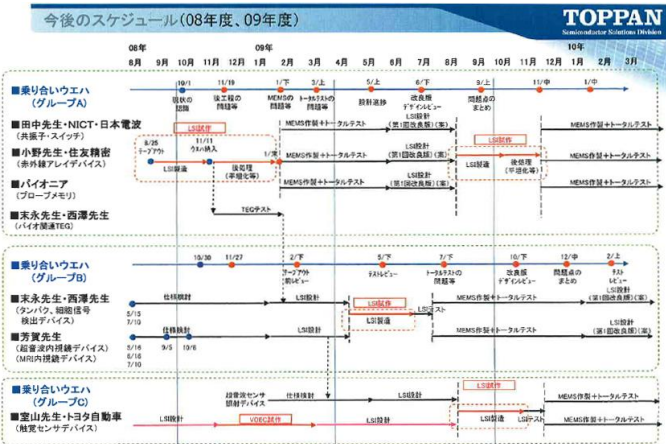
Room temperature Ga SLID (Solid-Liquid Inter-Diffusion bonding) (left: bonding interface, right: electroplating)

Reference : J. Frömel, Y.-C. Lin, M. Wiemer, T. Gessner and M. Esashi, Low Temperature Metal Interdiffusion Bonding for Micro Devices, 2012 3rd IEEE International Workshop on Low Temperature Bonding for 3D Integration (LTB-3D), Tokyo (2012, 22-23 May) 163

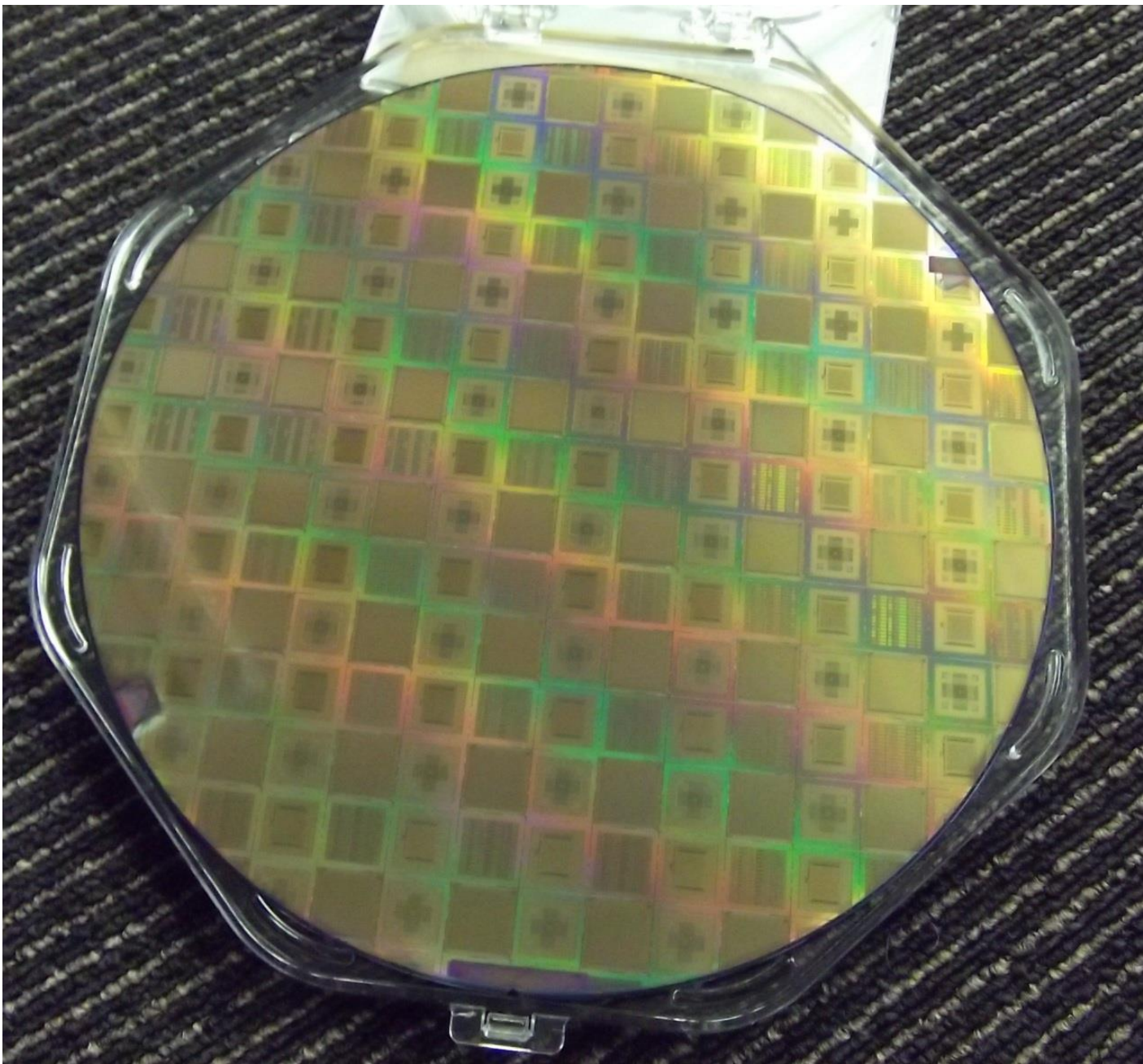
E6 Shared CMOS LSI wafer (Special Coordination Funds for Promoting Science and Technology, Formation of Innovation Center for Fusion of Advanced Technologies)



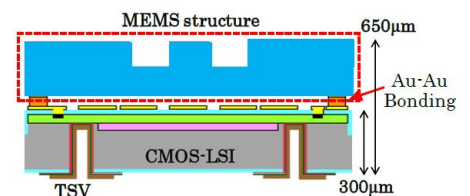
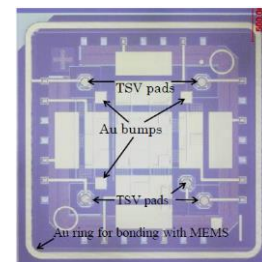
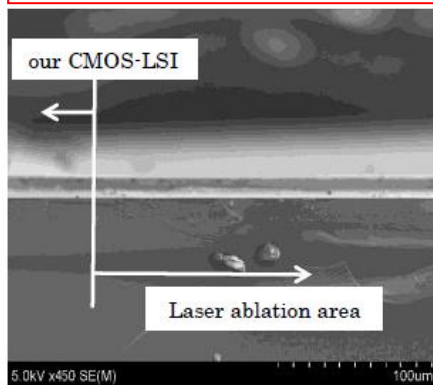
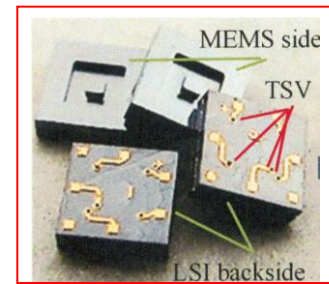
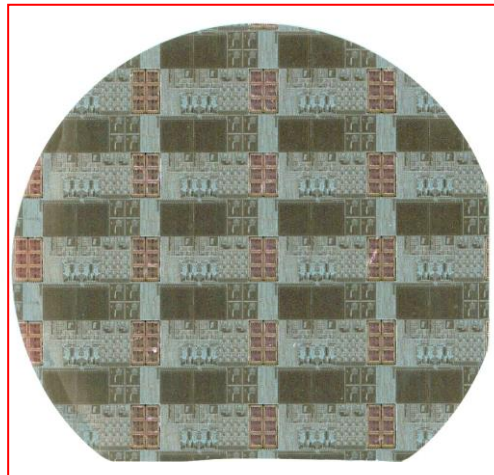
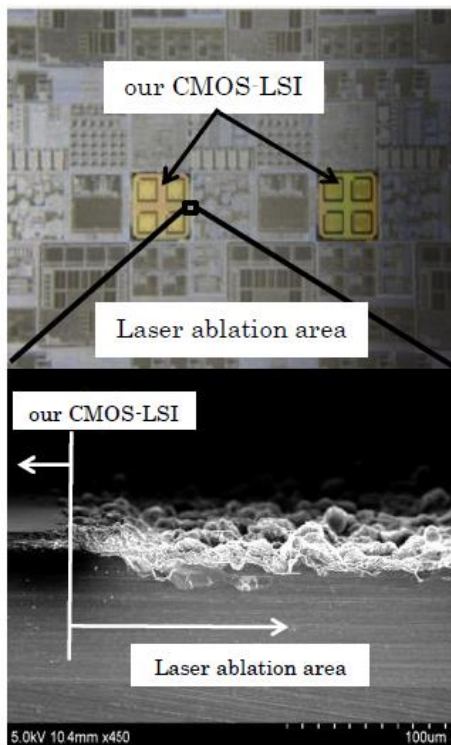
Company A	Company B
Project C	Project D



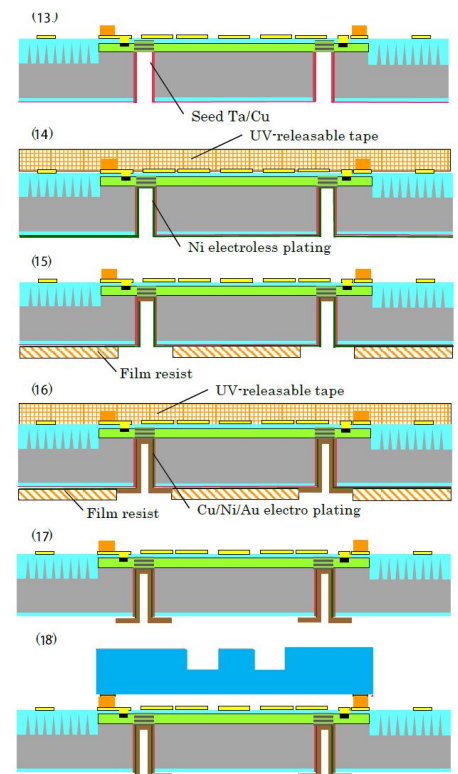
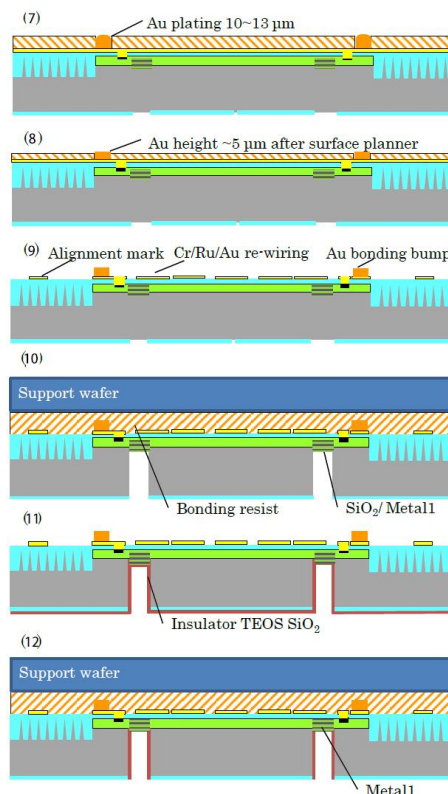
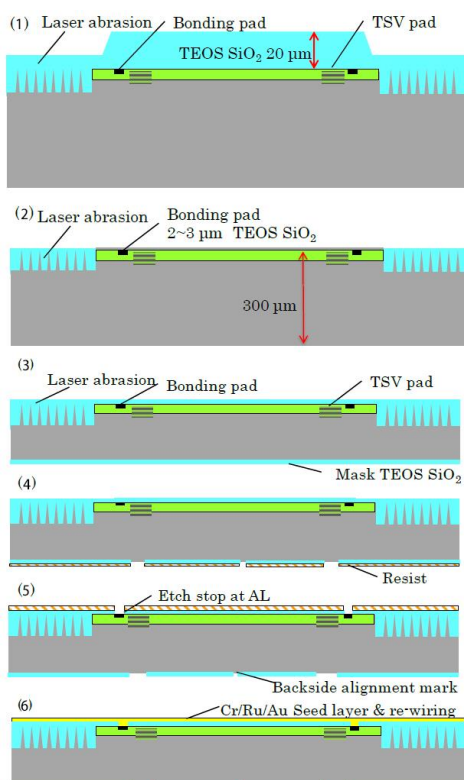
Shared CMOS wafer



E7 Laser-erased wafer process



Multi project wafer in which other chips are erased by laser and process Application to tactile sensor network chip for making MEMS and TSV on the CMOSLSI wafer

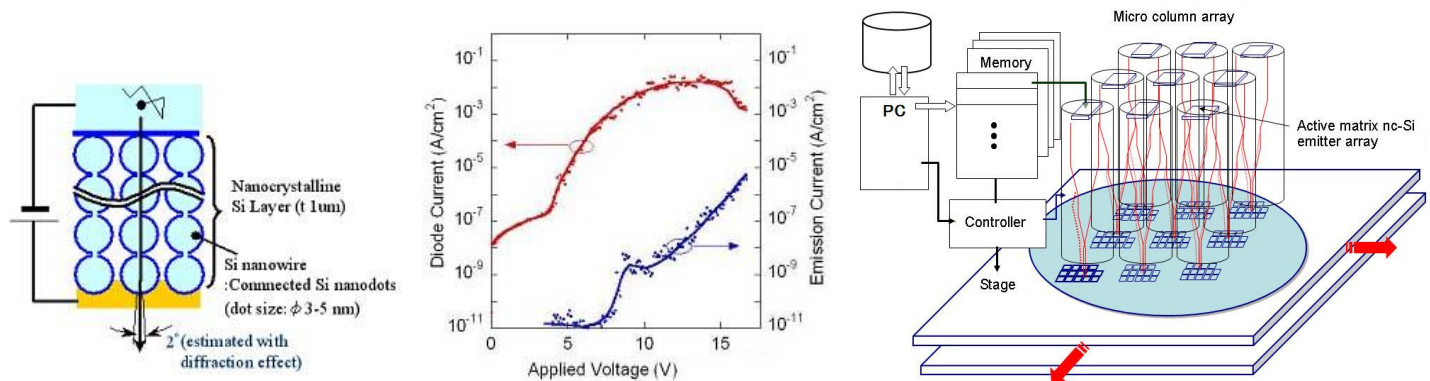


Fabrication process

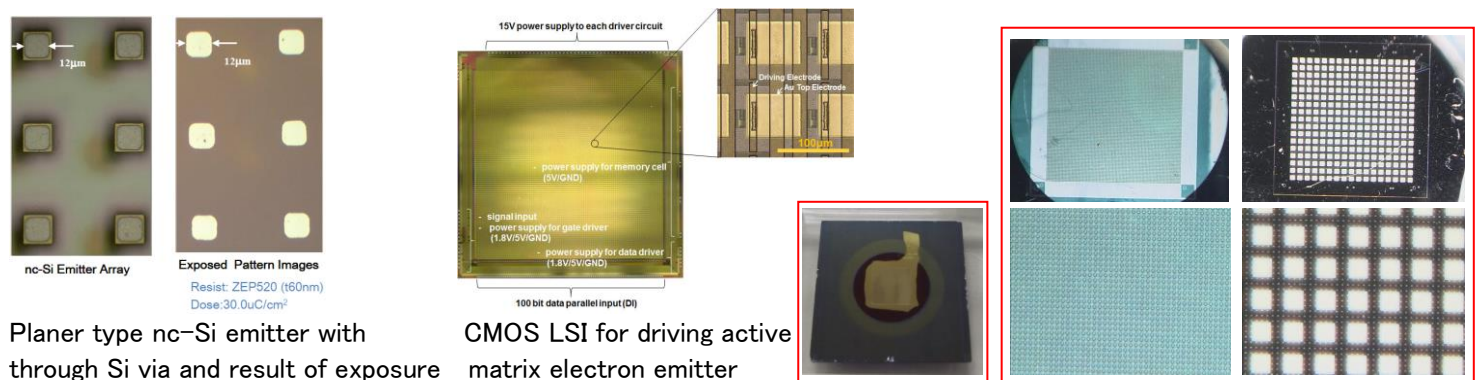
(Y.Suzuki, S.Tanaka et.al, Fabrication of Deep TSV in Laser-Erased CMOS-LSI Multi-project WAFER for Surface Mountable Integrated MEMS, Sensor Symp. 2016, 24pm2-B-6)

E8 Massive parallel electron beam write (MPEBW)

(Funding Program for World-Leading Innovative R&D on Science and Technology (FIRST))



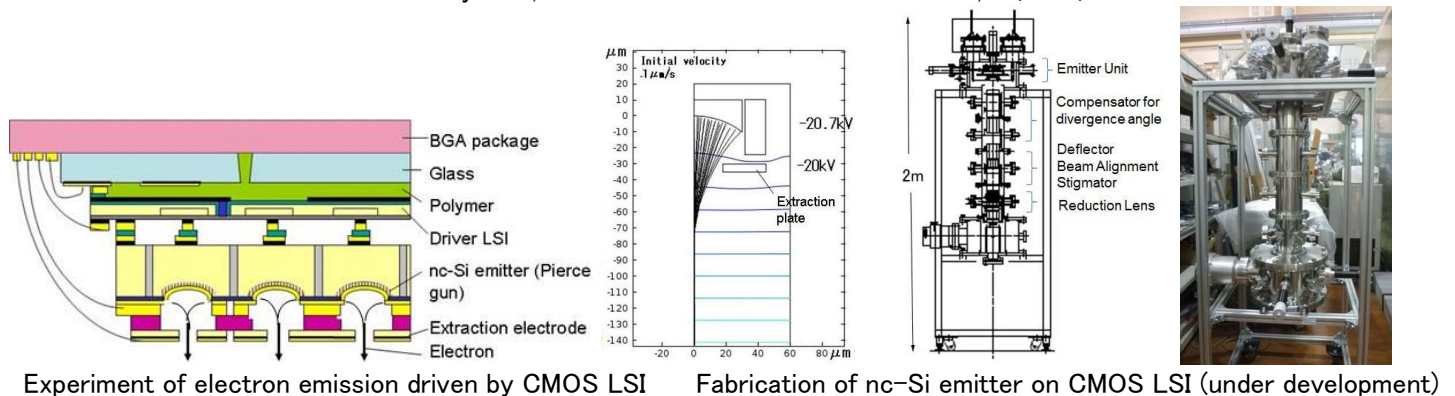
Principle of nano-crystalline (nc) Si emitter and concept of the electron beam exposure system using the nc-Si emitter



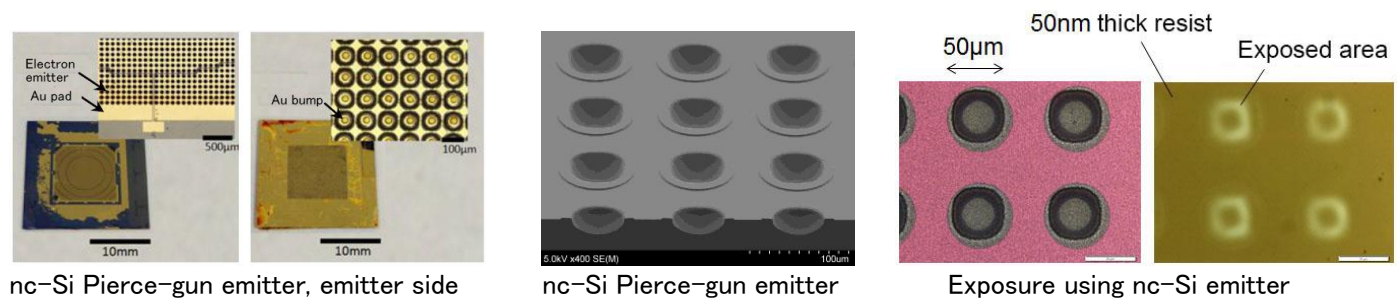
Planer type nc-Si emitter with through Si via and result of exposure CMOS LSI for driving active matrix electron emitter

N.Ikegami, T.Yoshida, A.Kojima, H.Ohyi, N.Koshida and M.Esashi.,

Active-Matrix nc-Si Electron Emitter Array for Massively Parallel Direct-Write Electron-Beam System, J. Micro/Nanolith. MEMS MOEMS 11, 3 (2012) 031406



Experiment of electron emission driven by CMOS LSI Fabrication of nc-Si emitter on CMOS LSI (under development)



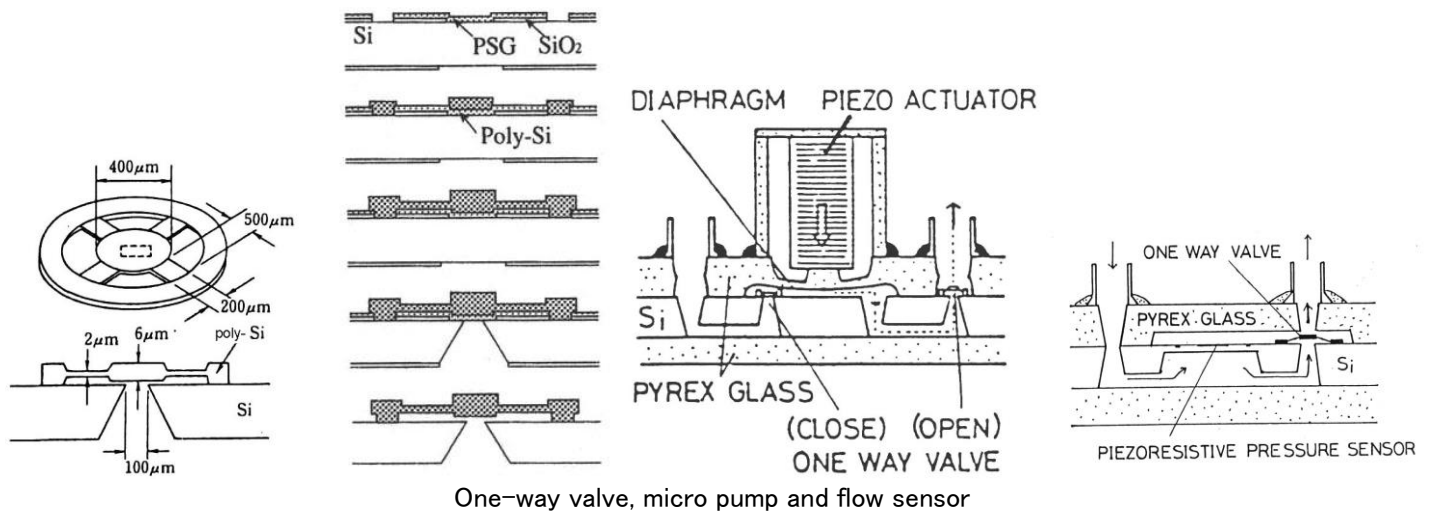
nc-Si Pierce-gun emitter, emitter side (left), bump side (right)

nc-Si Pierce-gun emitter

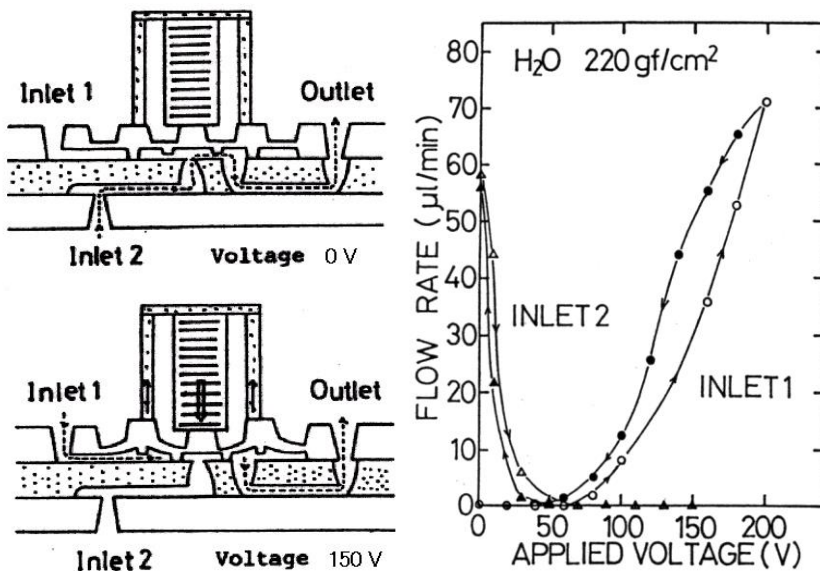
Exposure using nc-Si emitter

H.Nishino, S.Yoshino, S.Tanaka, M.Esashi, A.Kogima, N.Ikegami, N.Koshida, Basic study for fabrication of integrated Pierce-gun type area electron emitter for massive parallel electron beam exposure system, 2013 IEEJ convention, (2013/3/20 Nagoya) 3-127 (in Japanese)

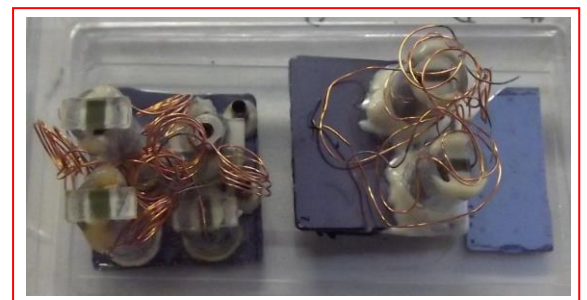
E9 Micro pump, micro valve and chemical analysis system for liquid



Reference : S.Shoji, M.Esashi, Fabrication of a Micro-pump for Integrated Chemical Analysing Systems, Trans. ICIEC, J71-C (1988) pp.1705-1711

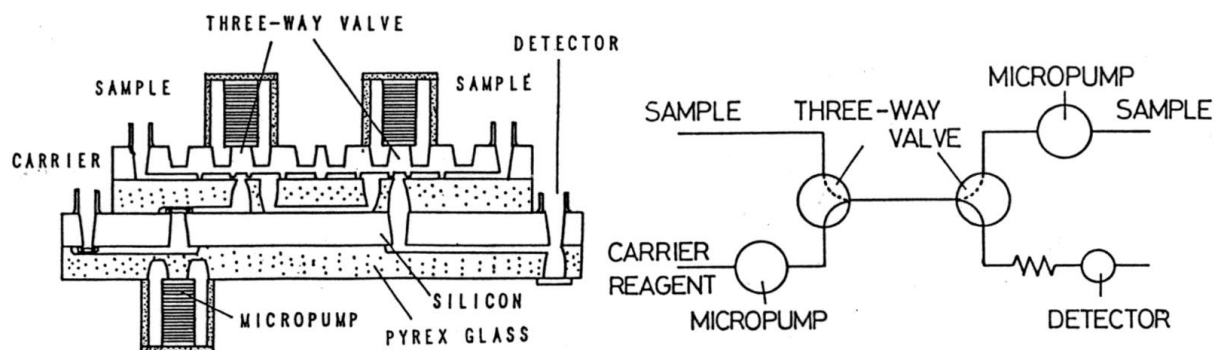


Tree-way valve



On-chip Flow-injection analysis system and micro pump

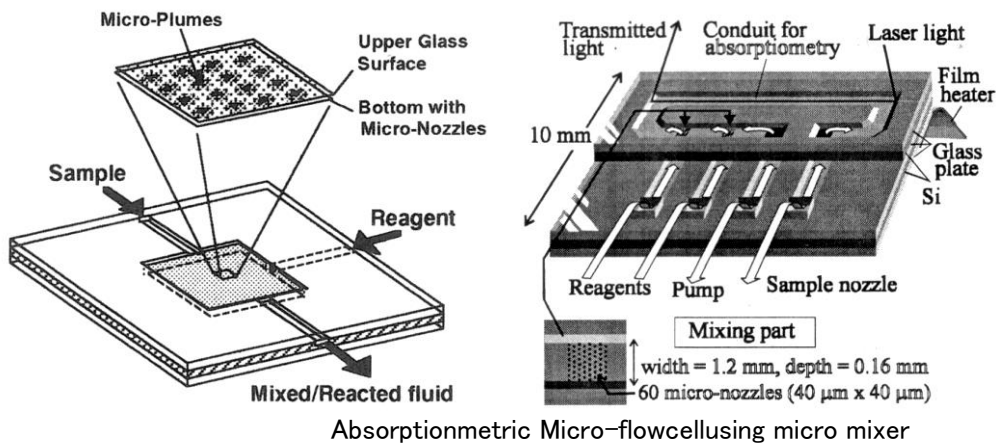
Reference : S.Shoji, S.Nakagawa and M.Esashi, Micropump and Sample-injector for Integrated Chemical Analyzing Systems, Sensors and Actuators, A21-A23 (1990) pp.189-192



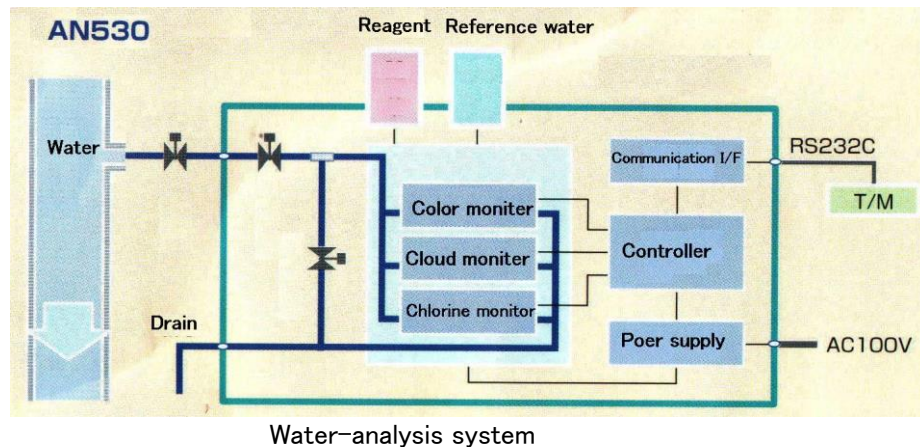
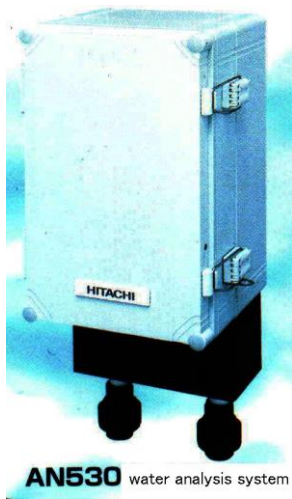
Flow injection analysis system integrated on a chip

Reference : S.Nakagawa, S.Shoji and M.Esashi, A Micro Chemical Analyzing System Integrated on a Silicon Wafer, Proc. of the Micro Electro Mechanical Systems'90 (1990) pp.89-94

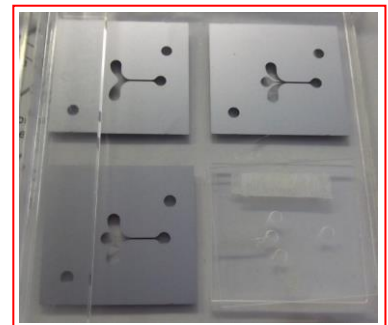
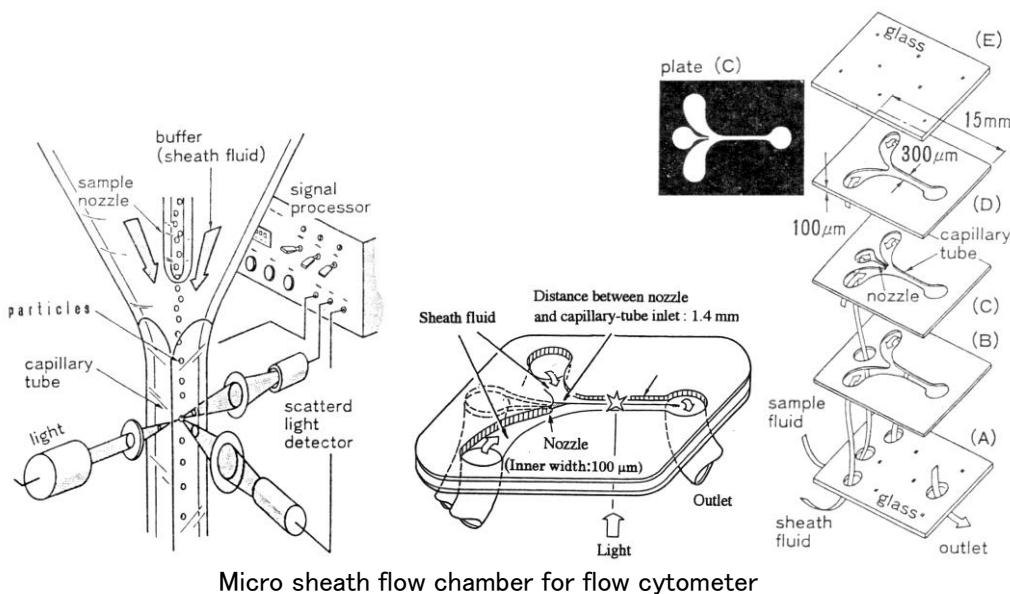
E10 Micro mixer and particle analysis (Hitachi)



Reference : R.Miyake, K.Tsuzuki, T.Takagi, K.Imai, A Highly Sensitive and Small Flow-type Chemical Analysis System with Integrated Absorptionmetric Micro-flowcell, Trans. IEE of Japan, 117-E (1997) pp.147-154

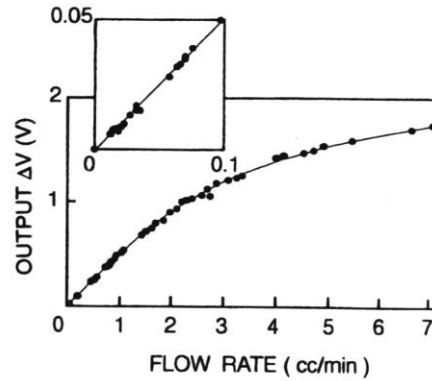
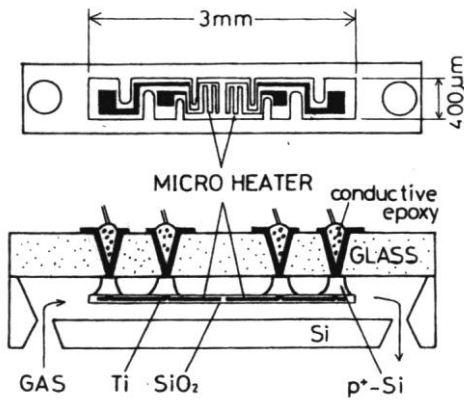


Reference : R.Miyake, H.Enoki, S.Mori, T.Ishihara, A Small Water-Analysis System with Micro-machined Flowcells, Technical Report IEE of Japan, CHS-00-7 (2000) pp.33-37



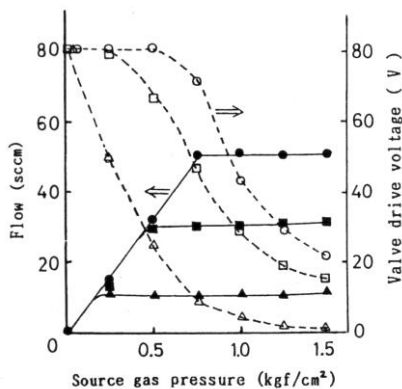
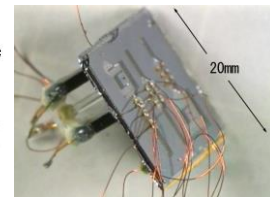
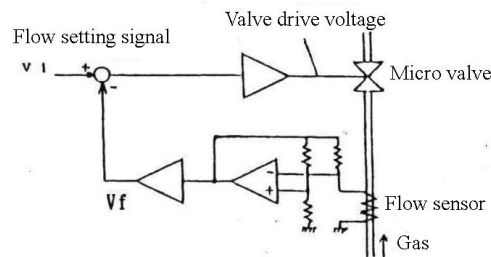
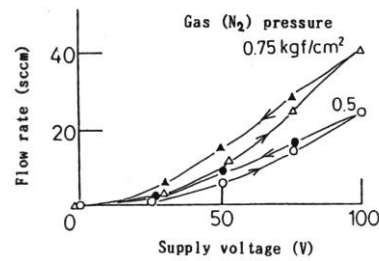
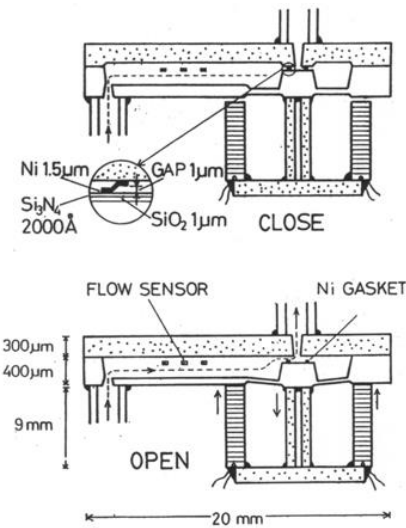
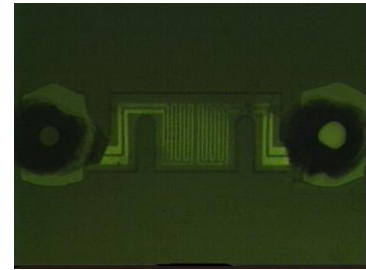
Reference : R.Miyake, H.Ohki and I.Yamazaki, A Development of Micro Sheath Flow Chamber, Proc. of IEEE MEMS' 91 (1991) pp.265-270

E11 Flow sensor and mass-flow controller for gas

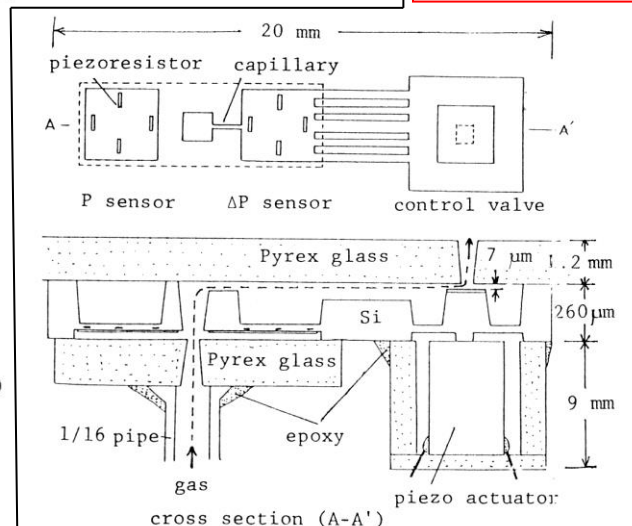
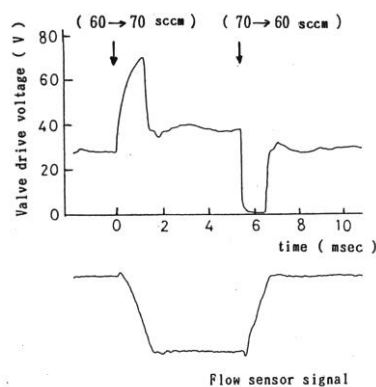


Thermal mass-flow sensor

Reference : M.Esashi, H.Kawai, K.Yoshimi, Differential Output Type Micro Flow Sensor, Trans. ICIEC, J75-C-II (1992) pp.738-742



Thermal mass-flow sensor + micro valve

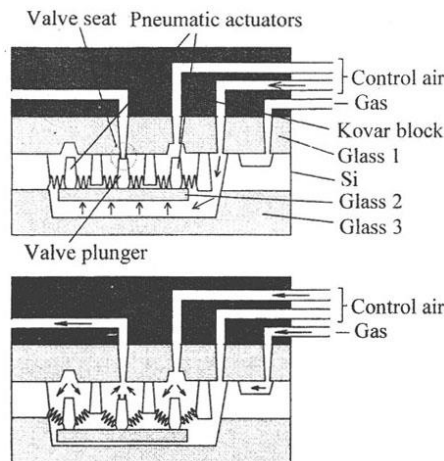
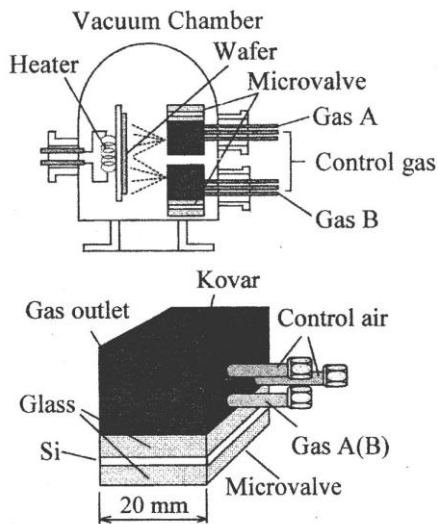


Differential pressure mass-flow sensor+micro valve

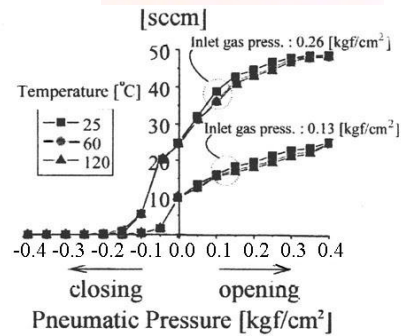
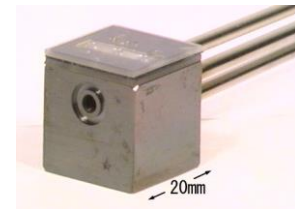
Integrated mass-flow controller

Reference : M.Esashi, S.Eoh, T.Matsuo and S.Choi, The Fabrication of Integrated Mass Flow Controller, Digest of Technical Papers, The 4th Int.Conf.on Solid State Sensors and Actuators (1987) pp.830-833

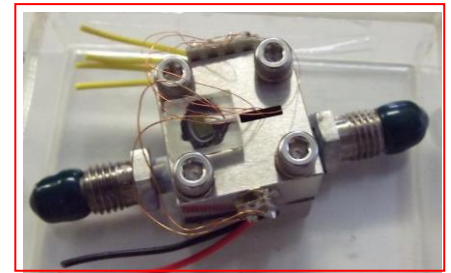
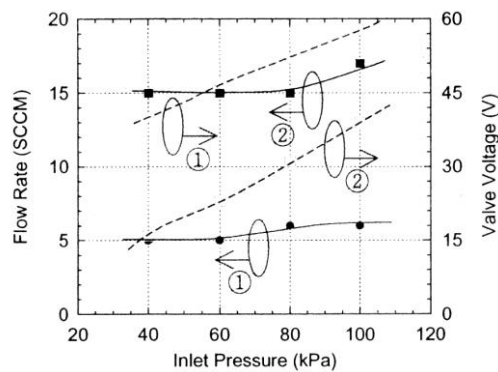
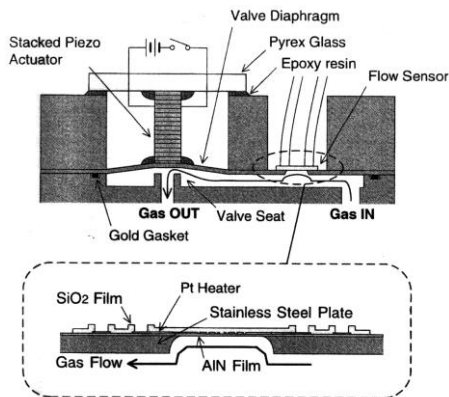
E12 Bakable micro valve and anticorrosive mass-flow controller



Bakable micro valve

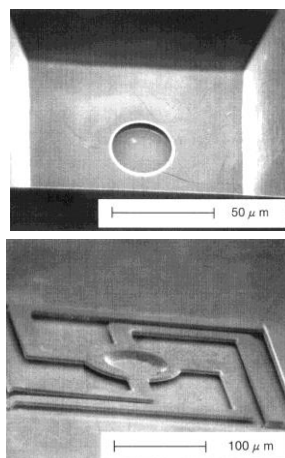
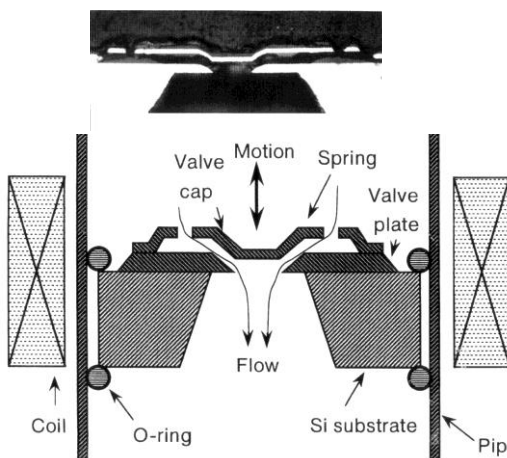


Reference : D.Y.Sim, T.Kurabayashi and M.Esashi, A Bakable Microvalve with a Kovar-Glass-Silicon-Glass Structure, J. of Micromechanics and Microengineering, 6 (1996) pp.266-271

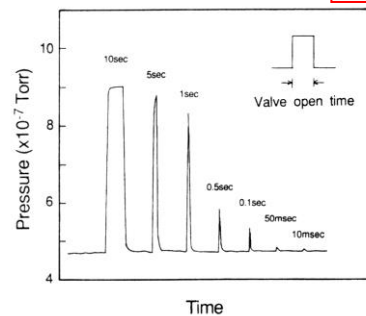


Anticorrosive mass-flow controller

Reference : K.Hirata, D.Y.Sim and M.Esashi, Stainless Steel-Based Integrated Mass-Flow Controller for Reactive and Corrosive Gases, Technical Digest of the Transducers' 01 (2001) pp.962-965

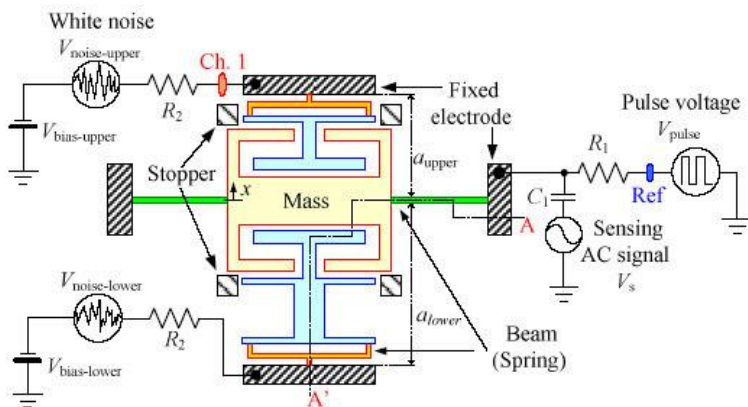


Electromagnetically driven microvalve (NTT)

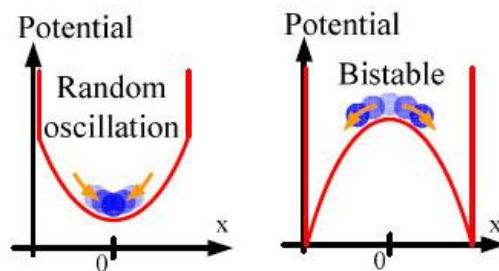
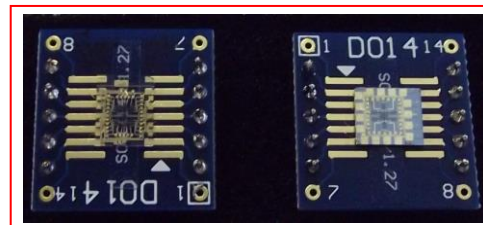


Reference : K.Yanagisawa, H.Kuwano and A.Tago, An Electromagnetically Driven Microvalve, Digest of Technical Papers, Transducers' 93 (1993) pp.102-105

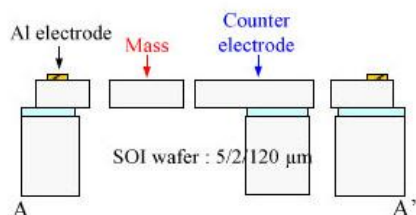
E13 Sensing in harsh environment



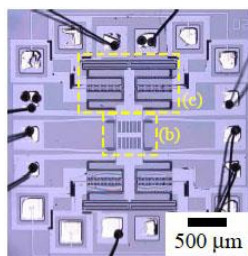
(a) Planar structure



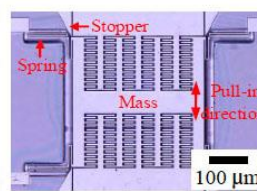
(a) V_{pulse} is zero or low. (b) V_{pulse} is high.



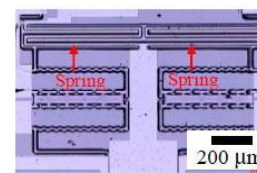
(b) Cross-sectional structure



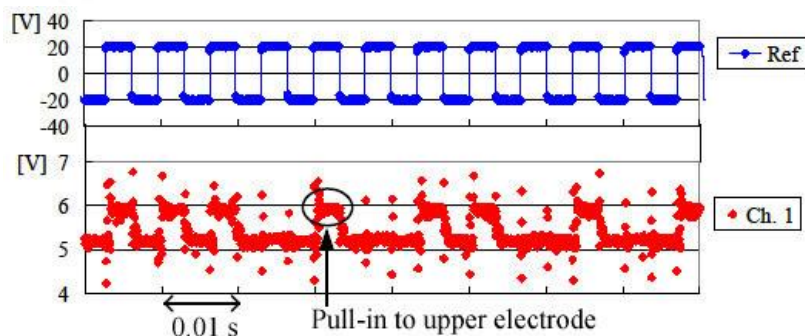
(a) Overall top view



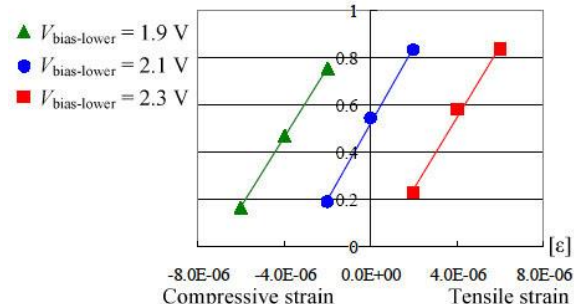
(b) Magnified view of the mass



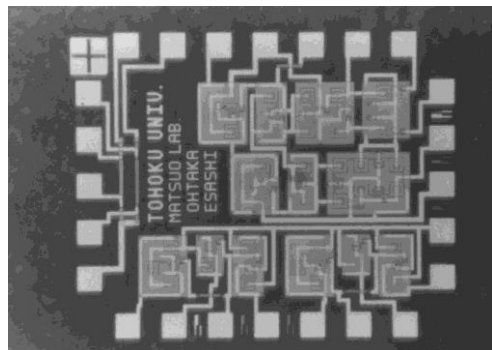
(c) Magnified view of springs supporting counter electrode



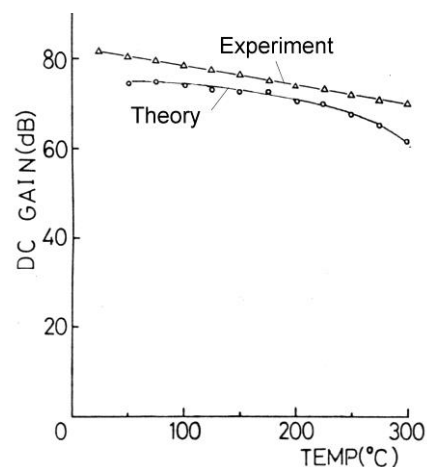
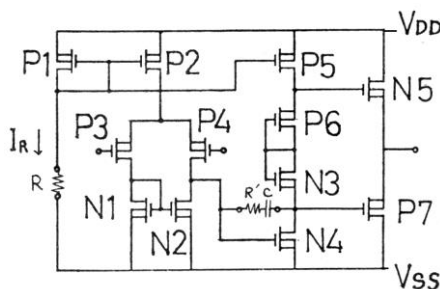
Stochastic sensor



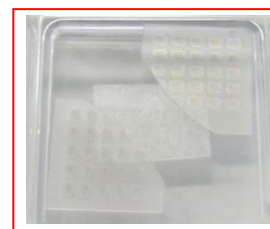
Reference : Y.Hatakeyama, M.Esashi and S.Tanaka, Stochastic Gravity Sensor with Robust Output Using White-Noise-Applied Vi-Stable State for Low S/N Environments, Tech. Digest IEEE MEMS 2012 (2012) pp.132-135



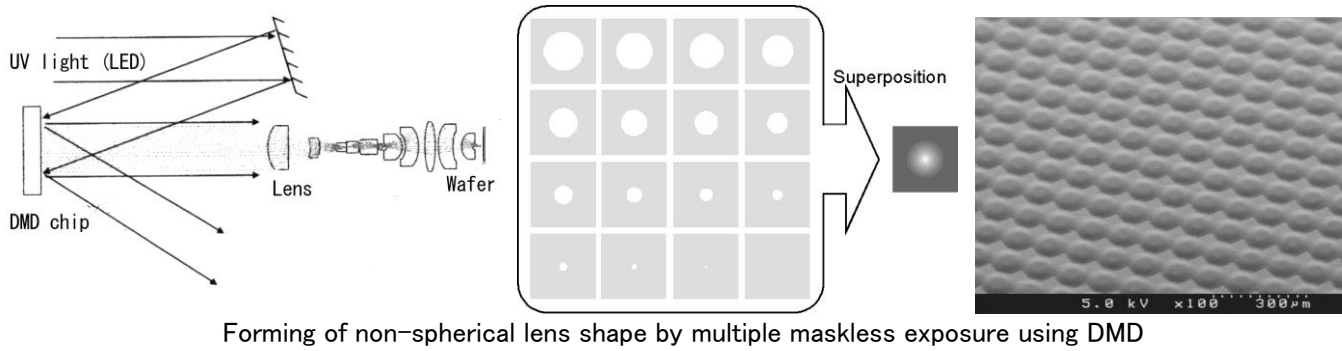
Operational amplifier for high temperature SOS (Silicon On Sapphire) OMOS



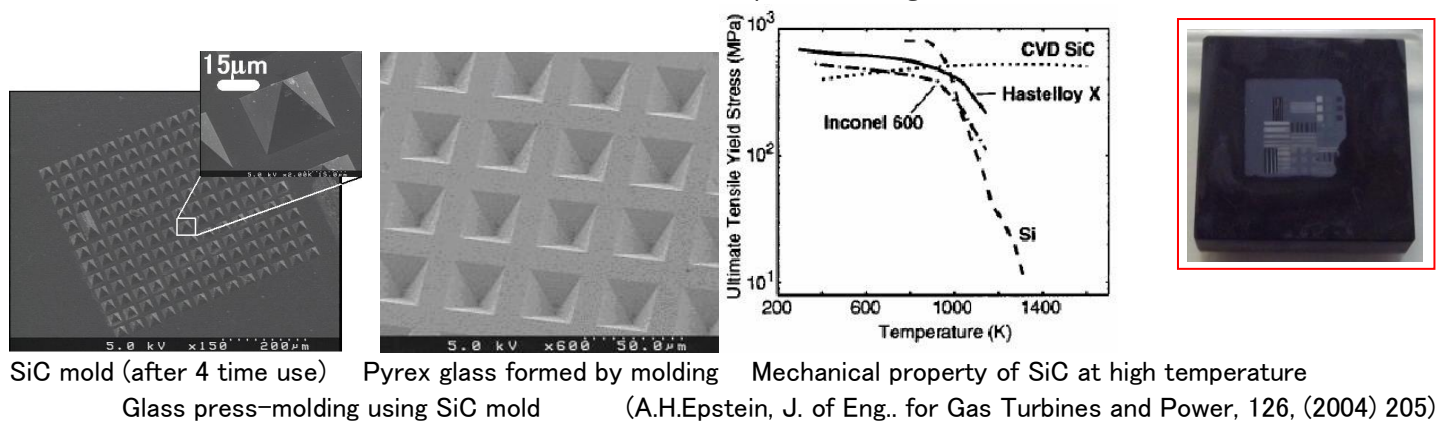
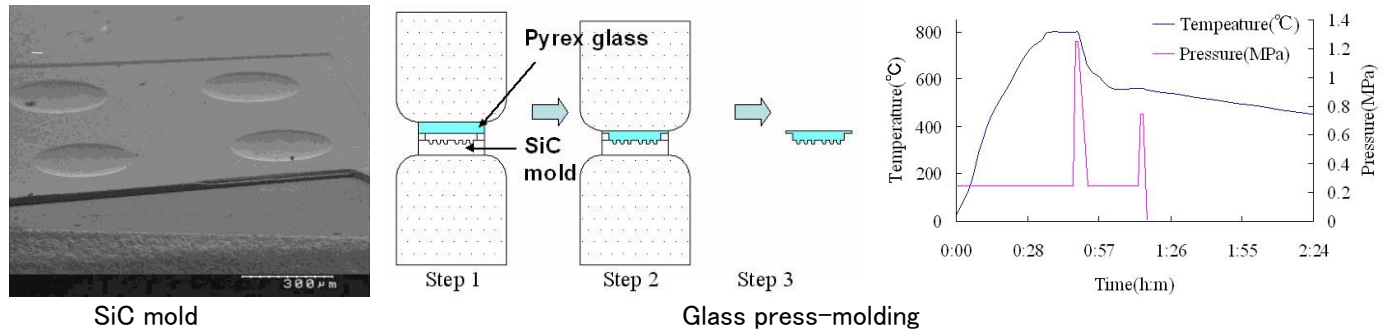
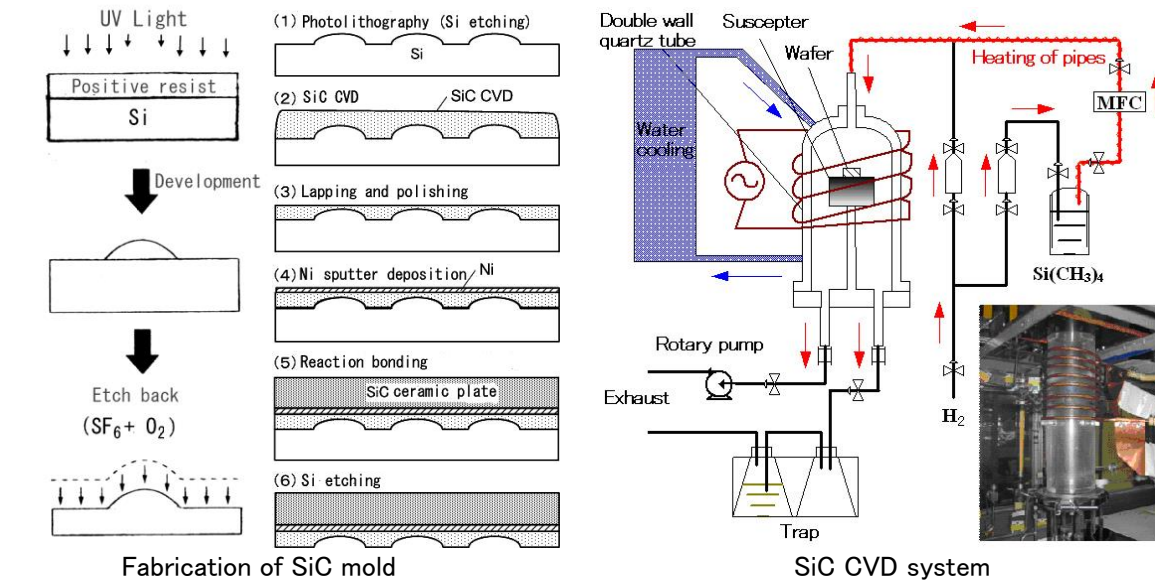
Reference : M.Esashi, S.Ohtaka, T.Matsuo, Fabrication of High Temperature Integrated Circuit and High Temperature Pressure Sensor, Technical Report, IEICE of Japan, SSD86-57 (1986) pp.67-74



E14 Silicon carbide (SiC) mold for glass press-molding



Reference : K.Totsu, K.Fujishiro, S.Tanaka and M.Esashi, Fabrication of Three-dimensional Microstructure Using Maskless Gray-scale Lithography, Sensors and Actuators A, 131 (2006) pp.387-392



Reference : K.-O. Min, S.Tanaka and M.Esashi, Glass Press Mold Fabricated by SiC APCVD, SiC-SiC Bonding and Silicon Lost Molding, Proceedings of the 21th Sensor Symposium (2004) pp.473-478